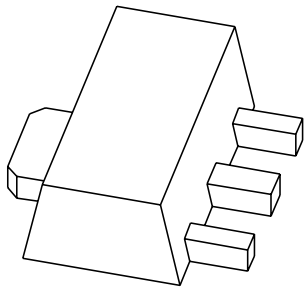


# DATA SHEET



## **BSR40; BSR41; BSR42; BSR43** NPN medium power transistors

Product specification  
Supersedes data of 1997 Apr 07

1999 Apr 28

## NPN medium power transistors

## BSR40; BSR41; BSR42; BSR43

## FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V).

## APPLICATIONS

- Thick and thin-film circuits
- Telephony and general industrial applications.

## DESCRIPTION

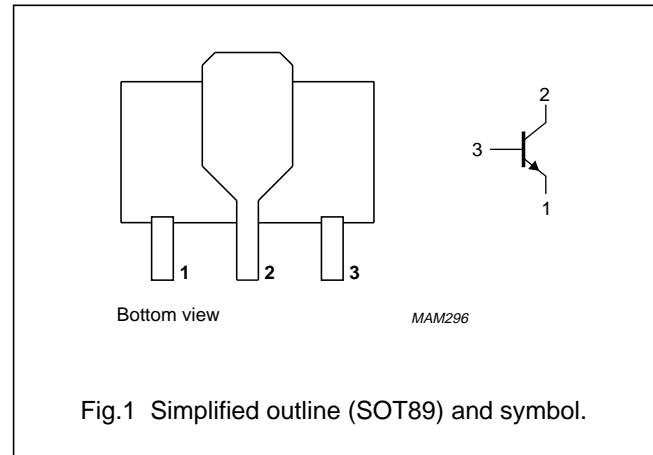
NPN medium power transistor in a SOT89 plastic package. PNP complements: BSR30; BSR3 and BSR33.

## MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BSR40	AR1	BSR42	AR3
BSR41	AR2	BSR43	AR4

## PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BSR40; BSR41		–	70	V
	BSR42; BSR43		–	90	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BSR40; BSR41		–	60	V
	BSR42; BSR43		–	80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	5	V
I <sub>C</sub>	collector current (DC)		–	1	A
I <sub>CM</sub>	peak collector current		–	2	A
I <sub>BM</sub>	peak base current		–	0.2	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	1.35	W
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

## Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 6 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

## NPN medium power transistors

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	93	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		13	K/W

## Note

- Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 6 cm<sup>2</sup>.  
For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 60\text{ V}$	–	100	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_j = 150\text{ °C}$	–	50	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	100	nA
$h_{FE}$	DC current gain BSR40; BSR42 BSR41; BSR43	$I_C = 100\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; \text{note 1}$	10 30	– –	
	DC current gain BSR40; BSR42 BSR41; BSR43	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}; \text{note 1}$	40 100	120 300	
	DC current gain BSR40; BSR42 BSR41; BSR43	$I_C = 500\text{ mA}; V_{CE} = 5\text{ V}; \text{note 1}$	30 50	– –	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	250	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	500	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	1	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	1.2	V
$C_c$	collector capacitance	$I_E = I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	12	pF
$C_e$	emitter capacitance	$I_C = I_E = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	90	pF
$f_T$	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	100	–	MHz
<b>Switching times (between 10% and 90% levels)</b>					
$t_{on}$	turn-on time	$I_{Con} = 100\text{ mA}; I_{Bon} = 5\text{ mA};$	–	250	ns
$t_{off}$	turn-off time	$I_{Boff} = -5\text{ mA}$	–	1	$\mu\text{s}$

## Note

- Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.01$ .

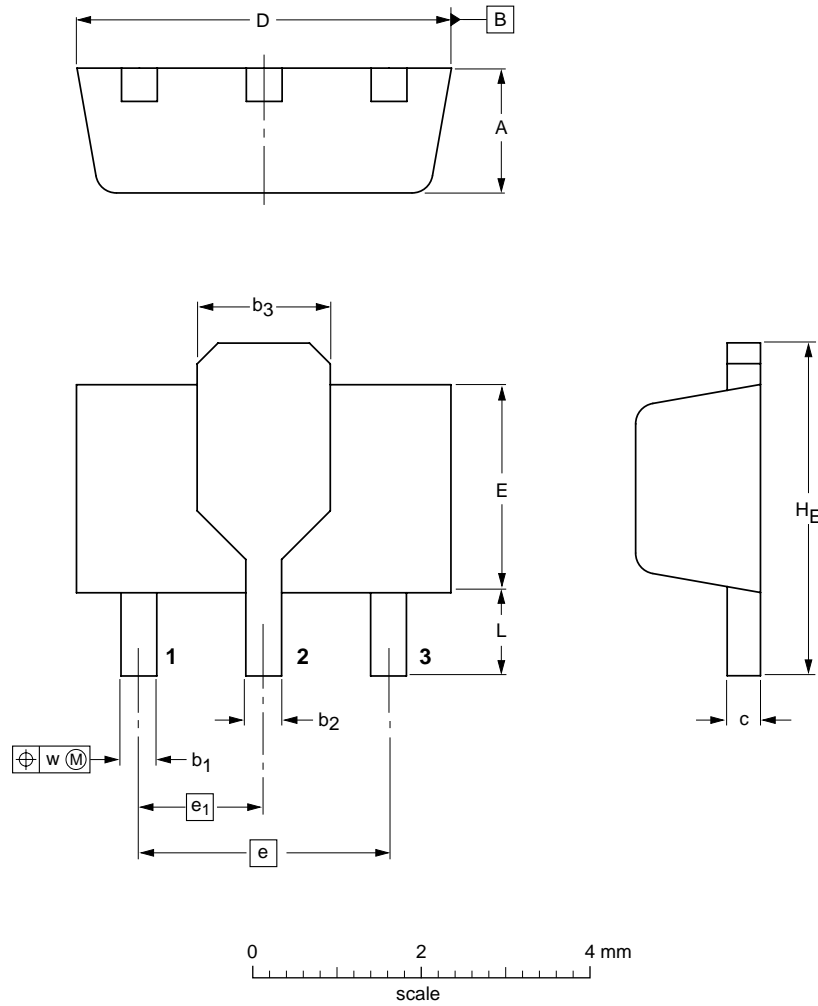
NPN medium power transistors

BSR40; BSR41; BSR42; BSR43

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b <sub>1</sub>	b <sub>2</sub>	b <sub>3</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L min.	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.37	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT89						97-02-28

## NPN medium power transistors

## BSR40; BSR41; BSR42; BSR43

**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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NPN medium power transistors

BSR40; BSR41; BSR42; BSR43

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**NOTES**

NPN medium power transistors

BSR40; BSR41; BSR42; BSR43

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**NOTES**

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